

# 6th Generation CoolSiC™

#### 650V SiC Schottky Diode

The CoolSiC<sup>TM</sup> generation 6 (G6) is the leading edge technology from Infineon for the SiC Schottky barrier diodes. The Infineon proprietary innovative G5 technology was enhanced in G6 by introducing further advancements like a novel Schottky metal system. The result is a family of products with improved efficiency over all load conditions, resulting from a lower figure of merit ( $Q_c \times V_F$ ). The CoolSiC<sup>TM</sup> Schottky diode 650 V G6 has been designed to complement our 600 V and 650 V CoolMOS<sup>TM</sup> 7 families, meeting the most stringent application requirements in this voltage range.

Table 1 Key performance parameters

Parameter	Value	Unit
$V_{RRM}$	650	V
$\overline{Q_C (V_R = 400 \text{ V})}$	9.6	nC
$\overline{E_C (V_R = 400 \text{ V})}$	1.6	μJ
$I_F (T_C \le 145  ^{\circ}\text{C}, D = 1)$	6	А
$V_F (I_F = 6 \text{ A}, T_j = 25 \text{ °C})$	1.25	V

Type / ordering Code	Package	Marking
IDH06G65C6	PG-TO220-2	D0665C6

# PG-TO220-2 CASE 1) Cathode 2) Anode 1 O O CASE

#### **Features**

- Best in class forward voltage (1.25 V)
- Best in class figure of merit  $(Q_c \times V_F)$
- High dv/dt ruggedness (150 V/ns)

#### **Benefits**

- System efficiency improvement
- System cost and size savings due to the reduced cooling requirements
- Enabling higher frequency and increased power density

#### **Potential Applications**

- Power factor correction in SMPS
- Solar inverter
- Uninterruptible power supply

#### **Product Validation**

Qualified for industrial applications according to the relevant tests of JEDEC (J-STD20 and JESD22)







# 6<sup>th</sup> Generation CoolSiC<sup>™</sup>

## IDH06G65C6



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# 1 Maximum ratings

Table 3 Maximum ratings

Davamatar	Complete	Values			l lmit		
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition	
	I <sub>F</sub>	-	_	6		$T_C \le 145 ^{\circ}\text{C}, D = 1$	
Continuous forward current		-	_	9		$T_C \le 125 ^{\circ}\text{C}, D = 1$	
		-	_	16		$T_C \le 25 ^{\circ}\text{C}, D = 1$	
Surge-repetitive forward current, sine halfwave <sup>1</sup>	$I_{F,RM}$	-	_	26	A	$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
Surge non-repetitive forward	1,	_	_	38		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
current, sine halfwave	$I_{F,SM}$	_	-	30		$T_C = 150  ^{\circ}\text{C}, t_p = 10  \text{ms}$	
Non-repetitive peak forward current	I <sub>F,max</sub>	-	-	410		$T_C = 25  ^{\circ}\text{C}, t_p = 10  \mu\text{s}$	
:24	( :2 -1+	_	_	7.2	A2-	$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
i <sup>2</sup> t value	∫i²dt	_	-	4.6	A <sup>2</sup> s	$T_C = 150  ^{\circ}\text{C}, t_p = 10  \text{ms}$	
Repetitive peak reverse voltage	$V_{RRM}$	_	_	650	V	<i>T<sub>C</sub></i> = 25 °C	
Diode dv/dt ruggedness	dv/dt	_	_	150	V/ns	V <sub>R</sub> = 0480 V	
Power dissipation	P <sub>tot</sub>	-	-	54	W	$T_C = 25^{\circ}\text{C}, R_{thJC,max}$	
Operating and storage temperature	$T_j$ $T_{stg}$	-55	-	175	°C	-	
Mounting torque	_	_	-	70	Ncm	M3 screw	

## 2 Thermal characteristics

Table 4 Thermal characteristics (PG-TO-220-2)

Davaraatav	Complete		Values		11	Note/Test condition
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition
Thermal resistance, junction- case	$R_{thJC}$	_	1.7	2.8	12 /\AI	_
Thermal resistance, junctionambient	$R_{thJA}$	_	_	62	K/W	leaded
Soldering temperature, wavesoldering only allowed at leads	$\mathcal{T}_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

Final Datasheet 3 Rev. 2.0, 2017-05-23

<sup>&</sup>lt;sup>1</sup> The surge-repetitive forward current test was performed with 1000 pulses (half-wave rectified sine with the 10 ms period).



## 3 Electrical characteristics

#### 3.1 Static characteristics

Table 5Static characteristics

Davamatav	Symbol Values Min. Typ. Max.	Values			l lmit	Note /Test condition
Parameter		Unit	Note/Test condition			
DC blocking voltage	$V_{DC}$	650	_	_		<i>T<sub>j</sub></i> = 25 °C
Diode forward voltage	$V_F$	_	1.25	1.35	V	$I_F = 6 \text{ A}, T_j = 25 ^{\circ}\text{C}$
		_	1.5	_		$I_F = 6 \text{ A}, T_j = 150 ^{\circ}\text{C}$
Reverse current	$I_R$	_	0.6	20	μΑ	$V_R = 420 \text{ V}, T_j = 25 \text{ °C}$
		_	20	_		$V_R$ = 420 V, $T_j$ = 125 °C
		_	46	_		$V_R = 420 \text{ V}, T_j = 150 \text{ °C}$

## 3.2 AC characteristics

Table 6 AC characteristics

Davamatav	Cumbal	Values			l lmia	Nata/Task Can dikian
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test Condition
Total capacitive charge	$Q_c$	-	9.6	_	nC	$V_R$ = 400 V, $T_j$ = 150 °C, di/dt = 200 A/ $\mu$ s, $I_F \le I_{F,MAX}$
		-	302	-	$PF = V_{R} = 1 \text{ V, } f = 1 \text{ MHz,}$ $T_{j} = 25 \text{ °C}$ $V_{R} = 300 \text{ V, } f = 1 \text{ MHz,}$ $T_{j} = 25 \text{ °C}$ $V_{R} = 600 \text{ V, } f = 1 \text{ MHz,}$ $T_{j} = 25 \text{ °C}$	,
Total capacitance	С	_	18	-		,
		-	17	_		· · · · · · · · · · · · · · · · · · ·



## 4 Diagrams

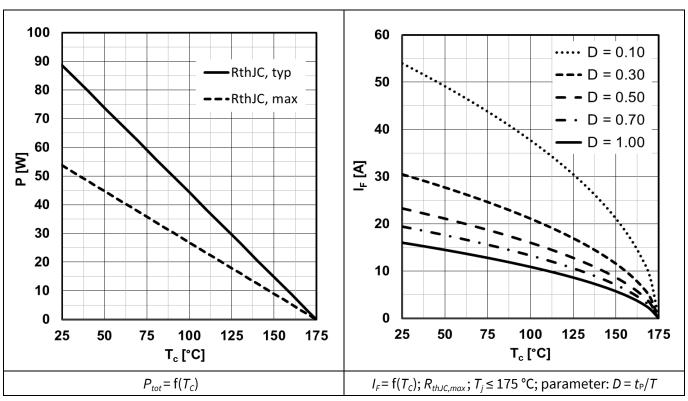


Figure 1 Power dissipation

Figure 2 Max. forward current

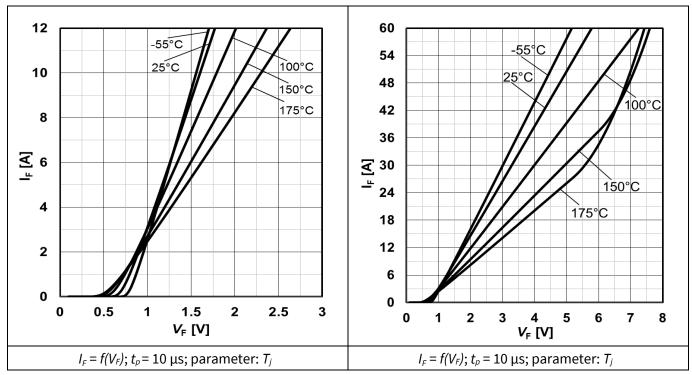


Figure 3 Typ. forward characteristics

Figure 4 Typ. forward characteristics in surge current



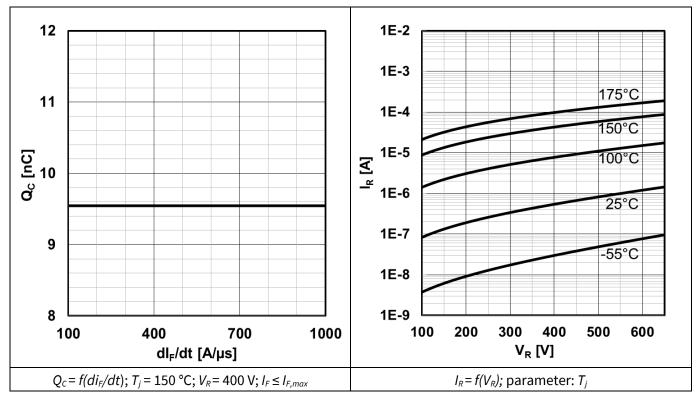


Figure 5 Typ. cap. charge vs. current slope

Figure 6 Typ. reverse current vs. reverse voltage

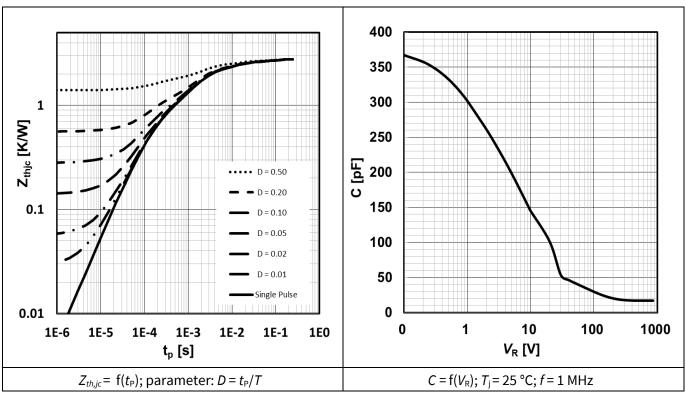


Figure 7 Max. transient thermal impedance

Figure 8 Typ. capacitance vs. reverse voltage



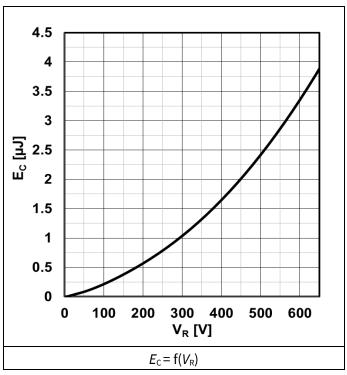


Figure 9 Typ. capacitance stored energy

# 5 Simplified forward characteristic

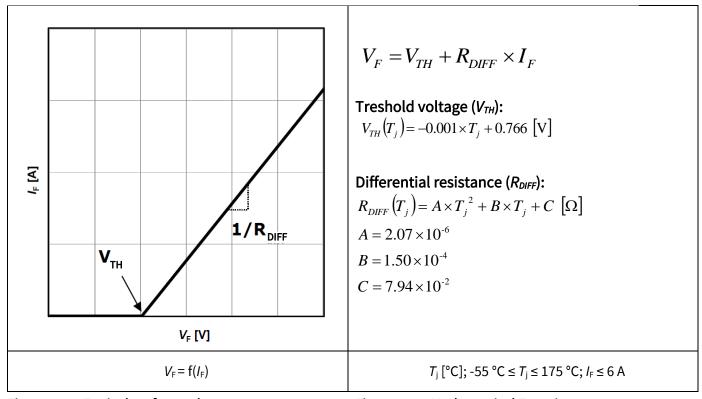


Figure 10 Equivalent forward current curve

Figure 11 Mathematical Equation



# 6 Package outlines

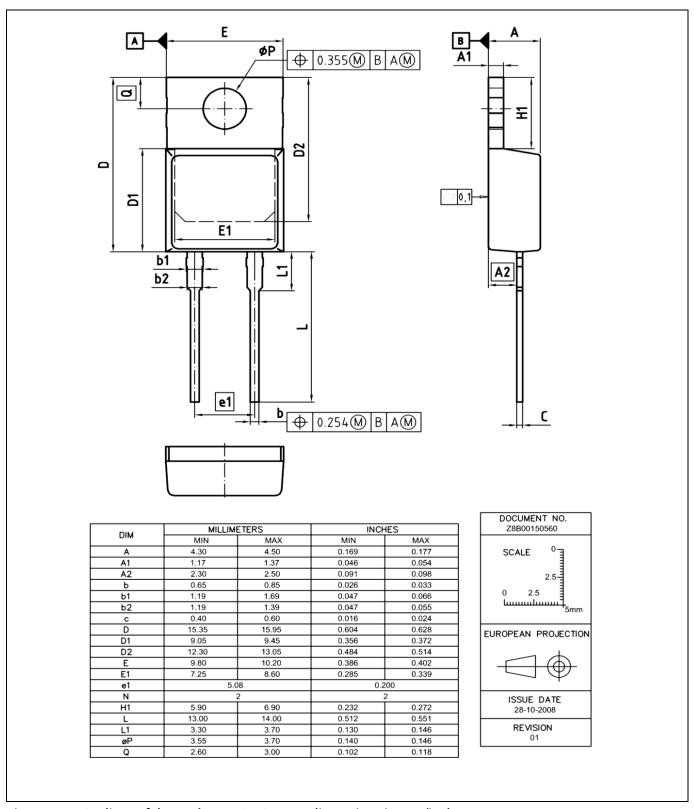


Figure 12 Outlines of the package PG-TO220-2, dimensions in mm/inches

# 6<sup>th</sup> Generation CoolSiC<sup>™</sup>

IDH06G65C6



## **Revision History**

## Major changes since the last revision

Revision	Date	Subject (major changes since last revision)
2.0	2017-05-23	Release of final version

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